

Title (en)
SEMICONDUCTOR COMPONENT

Title (de)
HALBLEITERBAUELEMENT

Title (fr)
COMPOSANT SEMI-CONDUCTEUR

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Application
EP 98948800 A 19980817

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Abstract (en)
[origin: DE19748523A1] The invention relates to a semiconductor component, comprising a semiconductor body (1) with two main surfaces, at least two electrodes (D, S), one of which is provided on a main surface, and alternating zones (3; 5, 7) of opposing conductor types which are situated in the semiconductor body (1) and which extend perpendicularly to the two main surfaces. When a voltage is applied to the two electrodes (D, S), the alternating zones (3; 5, 7) mutually discharge their charge carriers so that an essentially constant field strength is established in the semiconductor body (1) between the two electrodes. According to the invention, the alternating zones (3; 5, 7) contain at least one hollow space (6) which is preferably sealed by a glass layer (10).

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